

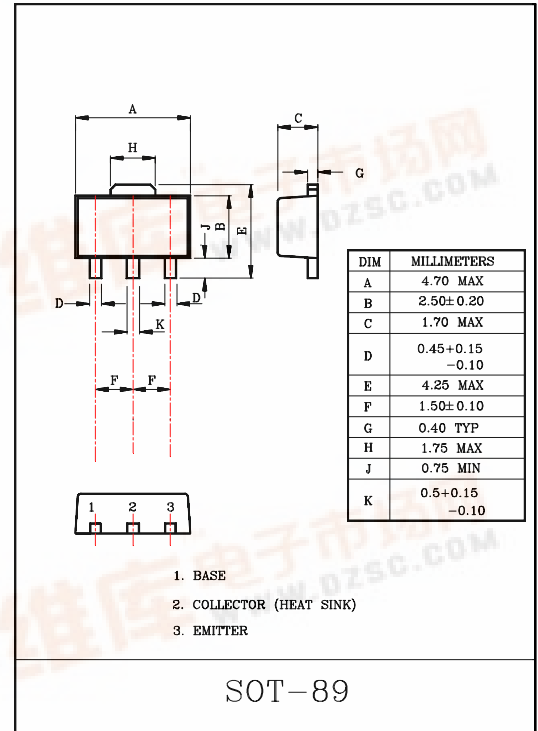
HIGH CURRENT APPLICATION.

FEATURES

- 1W (Mounted on Ceramic Substrate).
- Small Flat Package.
- Complementary to KTC4375.

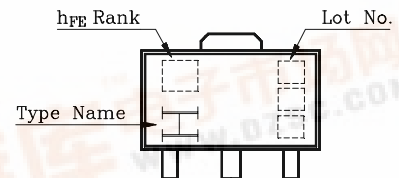
MAXIMUM RATINGS (Ta=25°C)

| CHARACTERISTIC | SYMBOL | RATING | UNIT |
|-----------------------------|------------------|---------|------|
| Collector-Base Voltage | V _{CB0} | -30 | V |
| Collector-Emitter Voltage | V _{CEO} | -30 | V |
| Emitter-Base Voltage | V _{EBO} | -5 | V |
| Collector Current | I _C | -1.5 | A |
| Base Current | I _B | -0.3 | A |
| Collector Power Dissipation | P _C | 500 | mW |
| | P _{C*} | 1 | W |
| Junction Temperature | T _j | 150 | °C |
| Storage Temperature Range | T _{stg} | -55~150 | °C |



P_{C*}:KTA1663 mounted on ceramic substrate(250mm²x0.8t)

Marking



ELECTRICAL CHARACTERISTICS (Ta=25°C)

| CHARACTERISTIC | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|--------------------------------------|------------------------|--|------|------|------|------|
| Collector Cut-off Current | I _{CBO} | V _{CB} =-30V, I _E =0 | - | - | -100 | nA |
| Emitter Cut-off Current | I _{EBO} | V _{EB} =-5V, I _C =0 | - | - | -100 | nA |
| Collector-Emitter Breakdown Voltage | V _{(BR)CEO} | I _C =-10mA, I _B =0 | -30 | - | - | V |
| Emitter-Base Breakdown Voltage | V _{(BR)EBO} | I _E =-1mA, I _C =0 | -5.0 | - | - | V |
| DC Current Gain | h _{FE} (Note) | V _{CE} =-2V, I _C =-500mA | 100 | - | 320 | |
| Collector-Emitter Saturation Voltage | V _{CE(sat)} | I _C =-1.5A, I _B =-0.03A | - | - | -2.0 | V |
| Base-Emitter Voltage | V _{BE} | V _{CE} =-2V, I _C =-500mA | - | - | -1.0 | V |
| Transition Frequency | f _T | V _{CE} =-2V, I _C =-500mA | - | 120 | - | MHz |
| Collector Output Capacitance | C _{ob} | V _{CB} =-10V, I _E =0, f=1MHz | - | - | 50 | pF |

Note : h_{FE} Classification O:100~200 , Y:160~320

KTA1663

